



**PRODUCT NAME :** 2SA1015 PNP General Purpose Transistor (Pack of 5)

**PRICE :** Rs 39.00

**SKU :** RM2117



NOTE: THE PRODUCT MAY BE DIFFERENT FROM IMAGE SHOWN ABOVE. Copyrights by Robomart.com

## DESCRIPTION

## Features

- Collector-Emitter Volt ( $V_{ce0}$ ): 50V
- Collector-Base Volt ( $V_{cb0}$ ): 50V
- Collector Current ( $I_c$ ): 0.15A
- $h_{fe}$ : 70-400 @ 2mA
- Power Dissipation ( $P_{tot}$ ): 400mW
- Current-Gain-Bandwidth ( $f_{total}$ ): 80MHz
- Type: PNP

**TOSHIBA**

**2SA1015**

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA1015

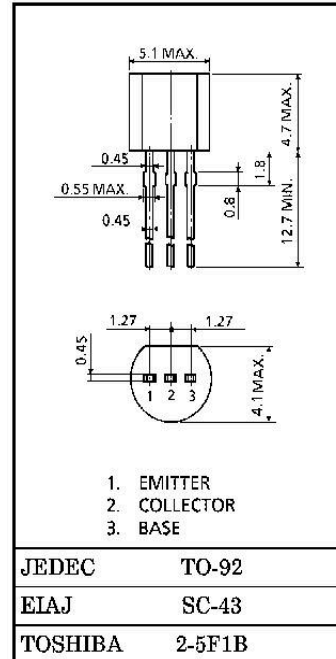
AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS  
 DRIVER STAGE AMPLIFIER APPLICATIONS

Unit in mm

- High Voltage and High Current.  
 :  $V_{CE0} = -50V$  (Min.),  $I_C = -150mA$  (Max.)
- Excellent  $h_{FE}$  Linearity  
 :  $h_{FE}(2) = 80$  (Typ.) at  $V_{CE} = -6V$ ,  $I_C = -150mA$   
 :  $h_{FE}(I_C = -0.1mA) / h_{FE}(I_C = -2mA) = 0.95$  (Typ.)
- Low Noise :  $NF = 1dB$  (Typ.) at  $f = 1kHz$
- Complementary to 2SC1815.

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-150	mA
Base Current	$I_B$	-50	mA
Collector Power Dissipation	$P_C$	400	mW
Junction Temperature	$T_j$	125	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~125	$^\circ C$



Weight : 0.21g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -50V$ , $I_E = 0$	—	—	-0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V$ , $I_C = 0$	—	—	-0.1	$\mu A$
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE} = -6V$ , $I_C = -2mA$	70	—	400	
	$h_{FE}(2)$	$V_{CE} = -6V$ , $I_C = -150mA$	25	80	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA$ , $I_B = -10mA$	—	-0.1	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -100mA$ , $I_B = -10mA$	—	—	-1.1	V
Transition Frequency	$f_T$	$V_{CE} = -10V$ , $I_C = -1mA$	80	—	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V$ , $I_E = 0$ , $f = 1MHz$	—	4	7	pF
Base Intrinsic Resistance	$r_{bb'}$	$V_{CE} = -10V$ , $I_E = 1mA$ , $f = 30MHz$	—	30	—	$\Omega$
Noise Figure	NF	$V_{CE} = -6V$ , $I_C = -0.1mA$ , $R_G = 10k\Omega$ , $f = 1kHz$	—	1.0	10	dB

Note :  $h_{FE}(1)$  Classification O : 70~140, Y : 120~240, GR : 200~400

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